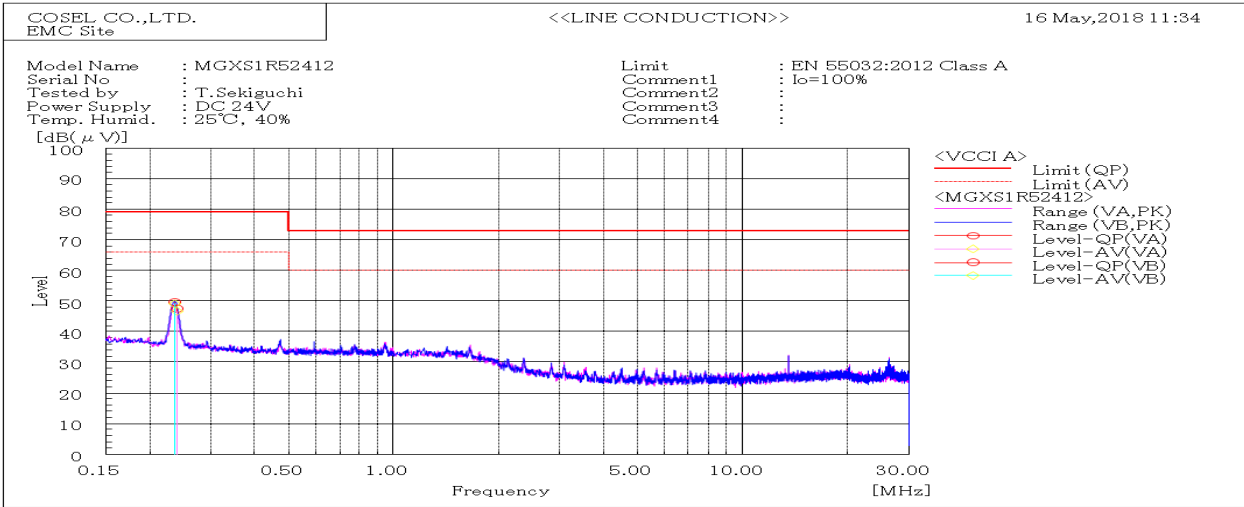
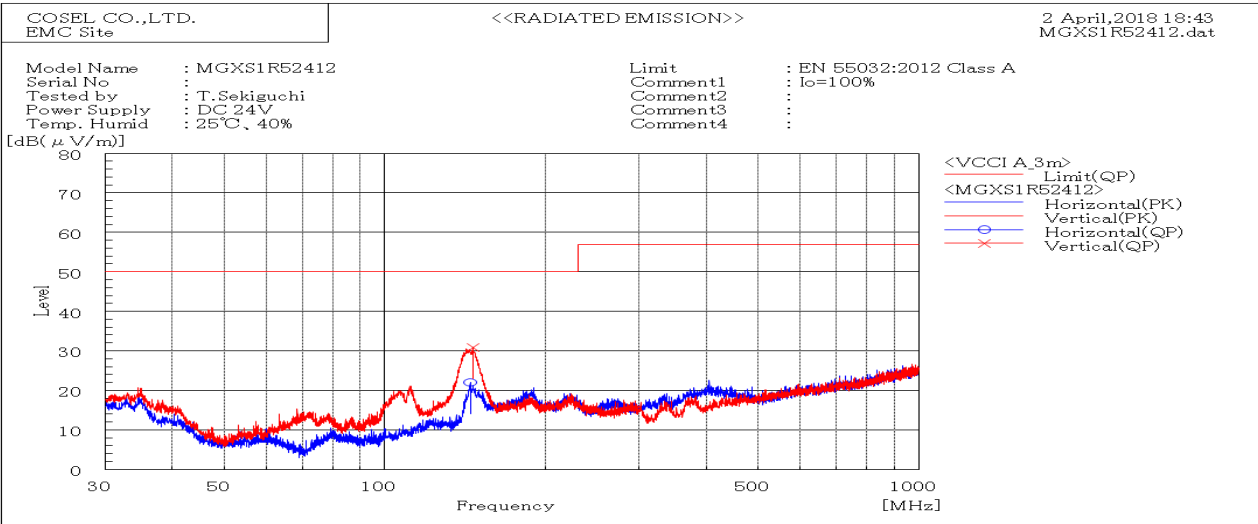


DATA SHEET		Date	18-Apr-18
Model	MGXS1R52412	Temp.	25 degreeC
Test	EMI Line conduction & Radiated emission	Humid.	40 %RH
		Tested by	T.Sekiguchi



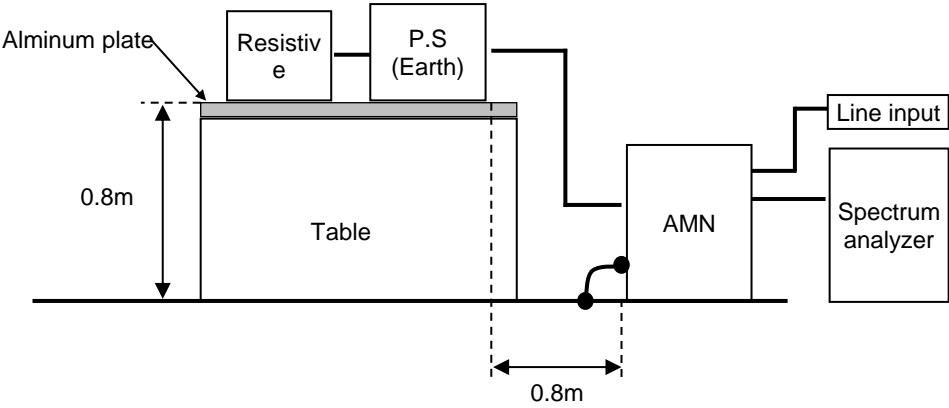
Frequency MHz	Line Phase	Level dB(μV)		Limit dB(μV)		Margin dB		Pass/Fail	Remark
		QP	AV	QP	AV	QP	AV		
0.23605	VB	49.6	49	79	66	29.4	17	Pass	
0.23923	VA	47.6	46.7	79	66	31.4	19.3	Pass	



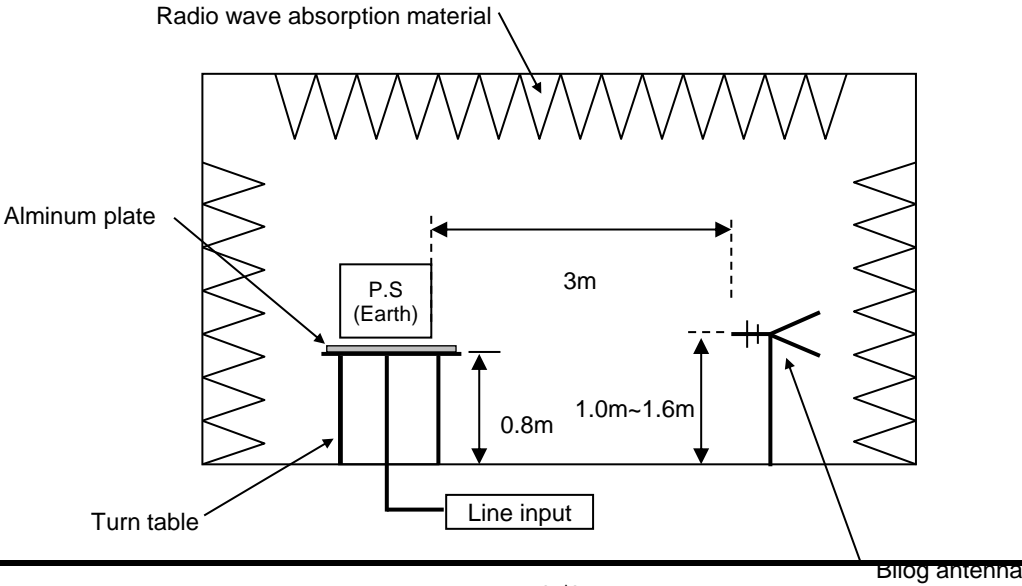
Frequency MHz	Polarization	Stability	Level dB(μV)	Limit dB(μV/m)	Margin dB(μV/m)	Pass/Fail	Height cm	Angle deg	Remark
			QP	QP	QP				
143.740	H	Stable	17.3	50.0	32.7	Pass	157	5	
146.579	V	Stable	28.1	50.0	21.9	Pass	100	325	

DATA SHEET		Date	18-Apr-18
Model	Circuit used for measurement	Temp.	25 degreeC
Test	EMI Line conduction & Radiated emission	Humid.	40 %RH
		Tested by	T.Sekiguchi

1. Line conduction



2. Radiated emission

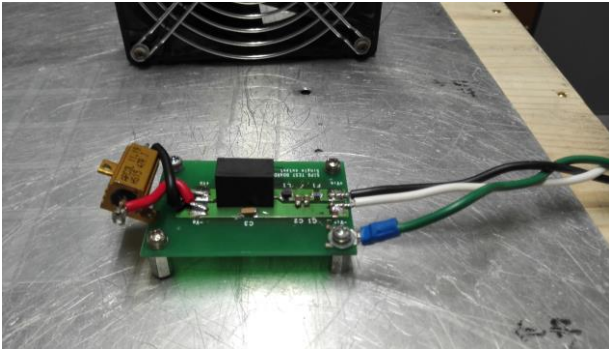


Conditions

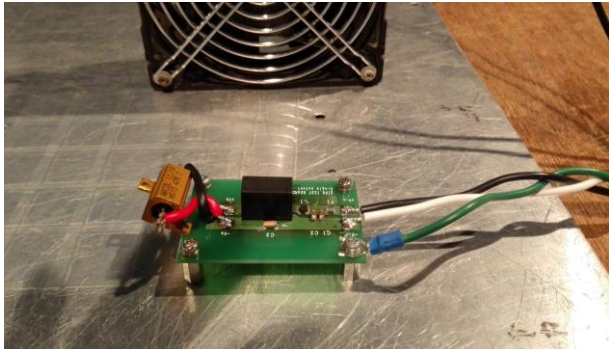
Test : EMI
Model Name : MGXS1R5□□

○Photographs of Test Set-Up

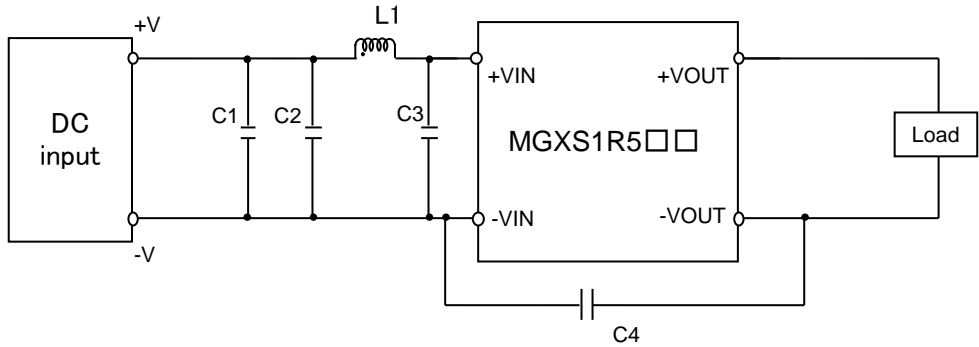
LINE CONDUCTION



RADIATED EMISSION



○Testing circuitry



- C1 : MGXS1R524□□ 100V 2.2 μ F Ceramic capacitor (GRM31CR72A225K MURATA MANUFACTURING)
- C2 : MGXS1R524□□ 100V 2.2 μ F Ceramic capacitor (GRM31CR72A225K MURATA MANUFACTURING)
- C3 : MGXS1R524□□ 100V 2.2 μ F Ceramic capacitor (GRM31CR72A225K MURATA MANUFACTURING)
- C4 : MGXS1R524□□ 2kV 1000pF Ceramic capacitor (GR442QR73D102K MURATA MANUFACTURING)
- L1 : MGXS1R524□□ 310mA 47 μ H Inductor(LQH32PN470MN0 MURATA MANUFACTURING)